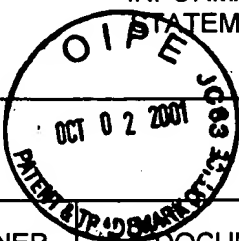


FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
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09/871,229INFORMATION DISCLOSURE
STATEMENT BY APPLICANTAPPLICANT
Lo et al.FILING DATE
May 31, 2001

GROUP



U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>HL</i>	4,718,070	06/1988	Liau et al.			
<i>HL</i>	4,935,939	06/1990	Liau et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
<i>HL</i>	Z. L. Liau, J. N. Walpole, "Surface-emitting GaInAsP/InP laser with low threshold current and high efficiency", Applied Physics Letters, vol. 46, no. 2, pp. 115-117, 1985.
<i>HL</i>	H. Saito, Y. Noguchi, "A reflection-type surface-emitting 1.3 μm GaInAsP/InP laser array with microcoated reflector", Japanese Journal of Applied Physics, vol. 28, pp. L1239-L1241, 1989.
<i>HL</i>	B. Stegmuller, H. Westermeier, W. Thulke, G. Franz, and D. Sacher, "Surface-emitting InGaAsP/InP distributed feedback laser diode at 1.53 μm with monolithic integrated microlens", IEEE Photonics Technology Letters, vol. 3, no. 9, pp. 776-778, 1991.

EXAMINER

Amanda Rodriguez

DATE CONSIDERED

8-2/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.